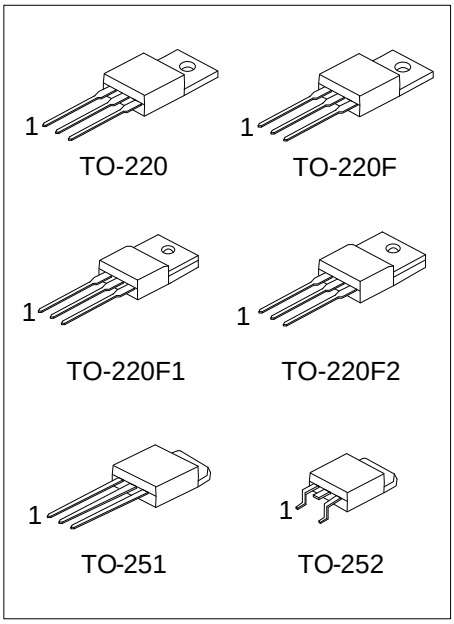
UTT18P06

Power MOSFET

-18.3A, -60V P-CHANNEL POWER MOSFET



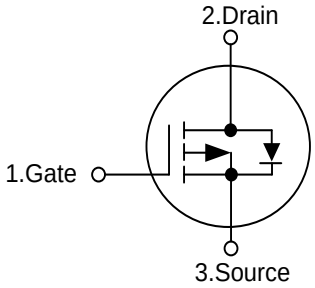
■ DESCRIPTION

The UTC **UTT18P06** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed, cost-effectiveness and minimum on-state resistance. It can also withstand high energy in the avalanche.

■ FEATURES

* $R_{DS(ON)} \leq 0.070\ \Omega$ @ V_{GS}= -10V, I_D= -18.3A
* High Switching Speed

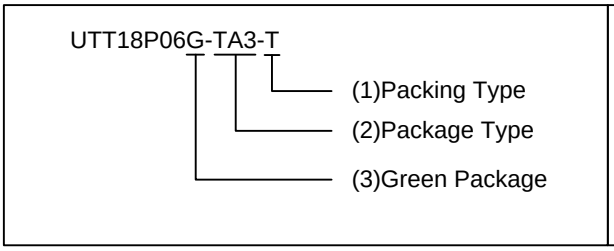
■ SYMBOL



■ ORDERING INFORMATION

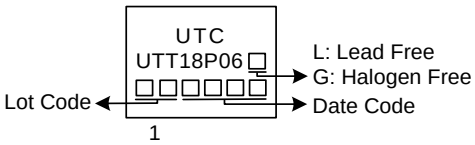
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT18P06L-TA3-T	UTT18P06G-TA3-T	TO-220	G	D	S	Tube
UTT18P06L-TF1-T	UTT18P06G-TF1-T	TO-220F1	G	D	S	Tube
UTT18P06L-TF2-T	UTT18P06G-TF2-T	TO-220F2	G	D	S	Tube
UTT18P06L-TF3-T	UTT18P06G-TF3-T	TO-220F	G	D	S	Tube
UTT18P06L-TM3-T	UTT18P06G-TM3-T	TO-251	G	D	S	Tube
UTT18P06L-TN3-R	UTT18P06G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2
TF3: TO-220F, TM3: TO-251, TN3: TO-252
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	-60	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current	Continuous	T_C=25°C	I_D	-18.3	A
	Pulsed		I_{DM}	-73.2	A
Single Pulsed Avalanche Current (L=0.1mH)			I_{AS}	-18.3	A
Single Pulsed Avalanche Energy (L=0.1mH) (Note 3)			E_{AS}	24.2	mJ
Power Dissipation (Note 4)	T_C=25°C	TO-220		90	W
		TO-220F TO-220F1 TO-220F2		39	W
		TO-251 TO-252		41	W
Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. Duty cycle ≤ 1 %.
4. See SOA curve for voltage derating.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	°C/W
	TO-251/TO-252		110	
Junction to Case	TO-220	θ_{JC}	1.38	°C/W
	TO-220F/TO-220F1 TO-220F2		3.19	
	TO-251/TO-252		3.05 (Note 3)	

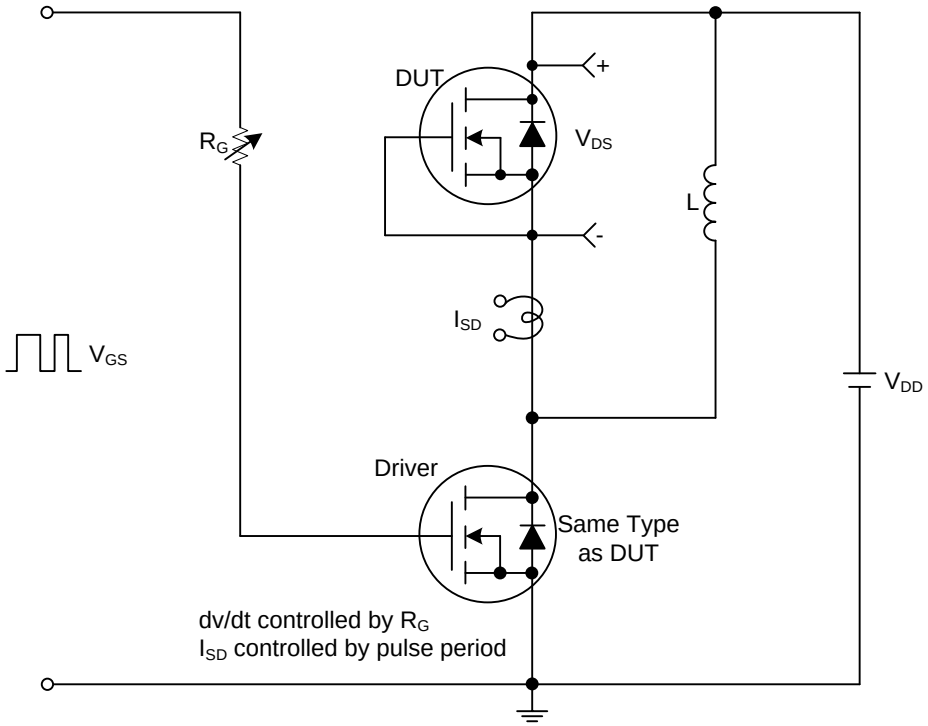
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

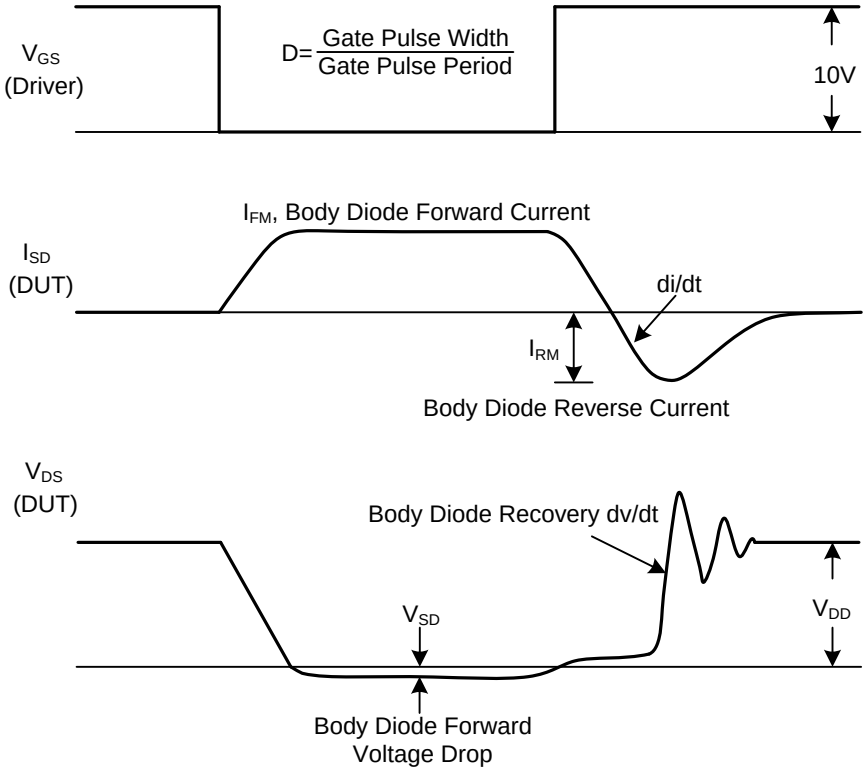
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=-250μA, V_{GS}=0V	-60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=-60V, V_{GS}=0V			-1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=-250μA	-1.0		-3.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=-10V, I_D=-18.3A (Note 1)		0.055	0.070	Ω
On State Drain Current (Note 1)		$I_{D(ON)}$	V_{GS}=-10V, V_{DS}=-5V	-30			A
DYNAMIC PARAMETERS (Note 2)							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=-25V, f=1.0MHz (Note 2)		840	1310	pF
Output Capacitance		C_{OSS}			95		pF
Reverse Transfer Capacitance		C_{RSS}			70		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=-10V, V_{DS}=-50V, I_D=-1.3A, I_G=100μA (Note 3)		35	40	nC
Gate to Source Charge		Q_{GS}			6		nC
Gate to Drain Charge		Q_{GD}			7.0		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=-30V, I_D=-0.5A, R_G=2.5Ω (Note 3)		50		ns
Rise Time		t_R			43		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			300		ns
Fall-Time		t_F			95		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C=25°C) (Note 2)							
Maximum Body-Diode Continuous Current		I_S				-18.3	A
Maximum Body-Diode Pulsed Current		I_{SM}				-73.2	A
Drain-Source Diode Forward Voltage		V_{SD}	I_F=-18.3A, V_{GS}=0V (Note 1)		-1.0	-1.5	V
Body Diode Reverse Recovery Time		t_{rr}	I_F=-18.3A, dI_F/dt=100A/μs		14	61	ns

Notes: 1. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
2. Guaranteed by design, not subject to production testing
3. Independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS



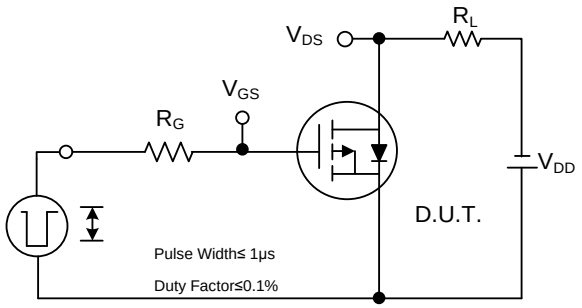
Peak Diode Recovery dv/dt Test Circuit



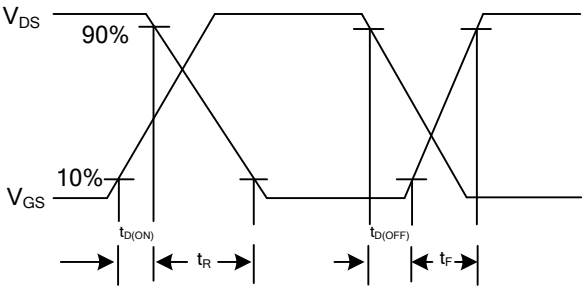
Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

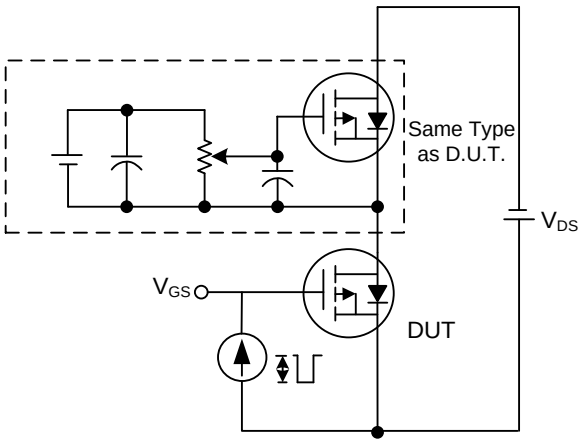
■ TEST CIRCUITS AND WAVEFORMS



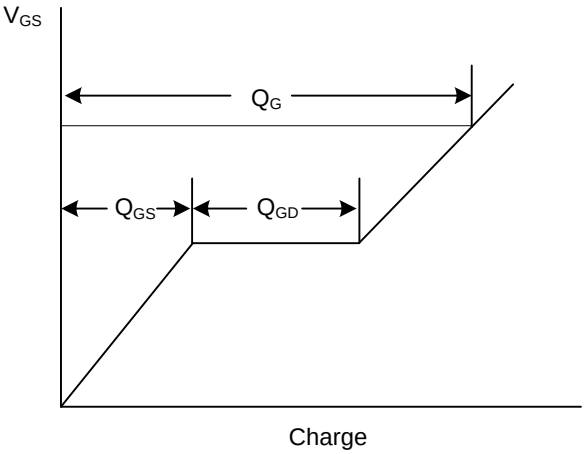
Switching Test Circuit



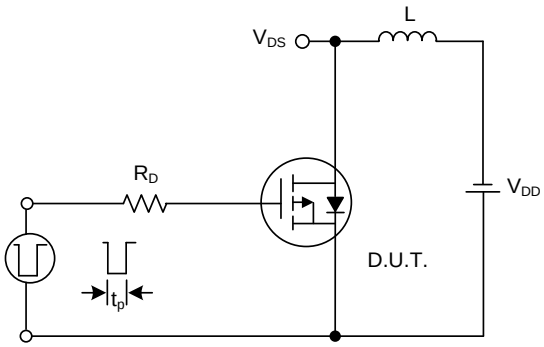
Switching Waveforms



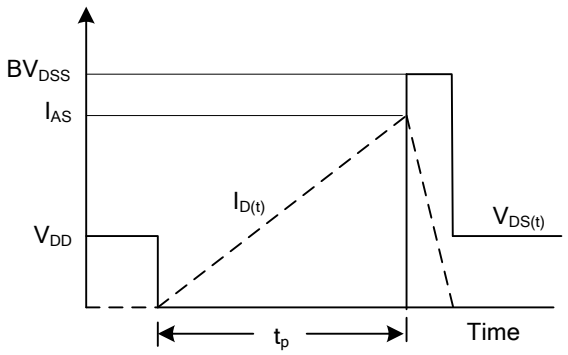
Gate Charge Test Circuit



Gate Charge Waveform



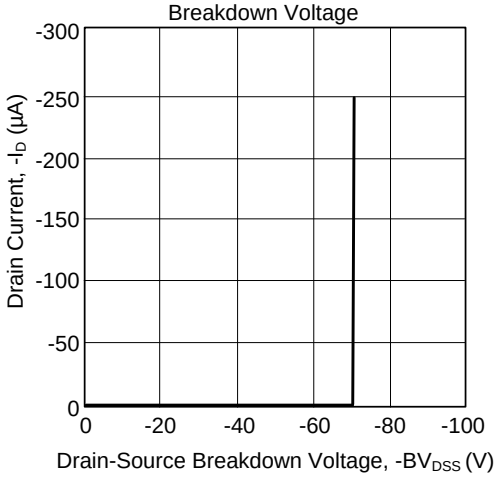
Unclamped Inductive Switching Test Circuit



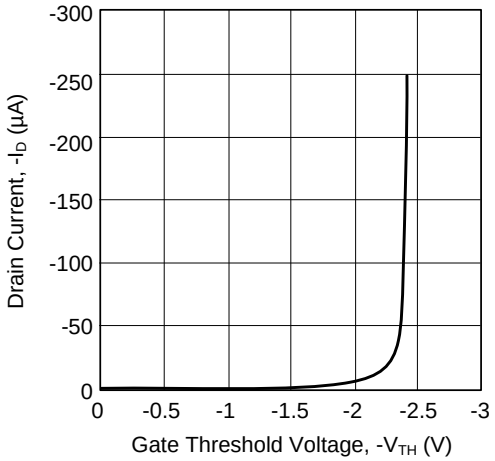
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

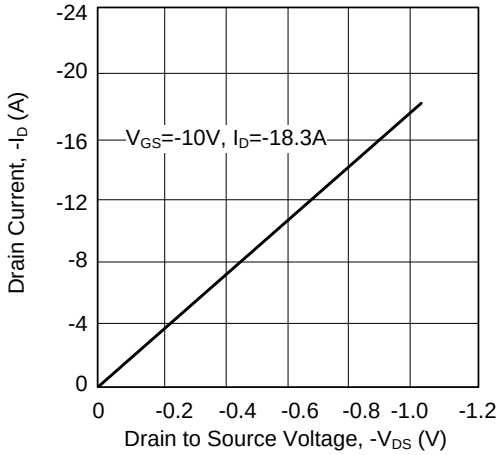
Drain Current vs. Drain-Source Breakdown Voltage



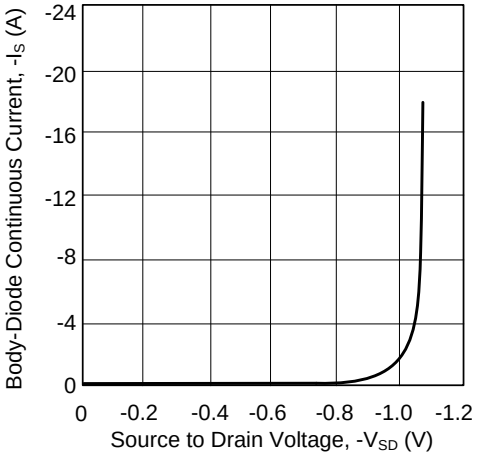
Drain Current vs. Gate Threshold Voltage



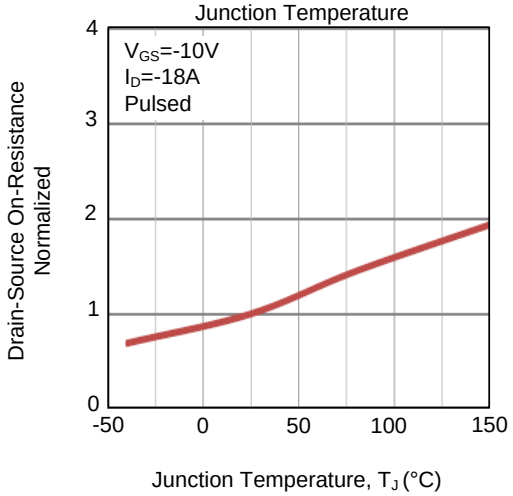
Drain-Source On-State Resistance Characteristics



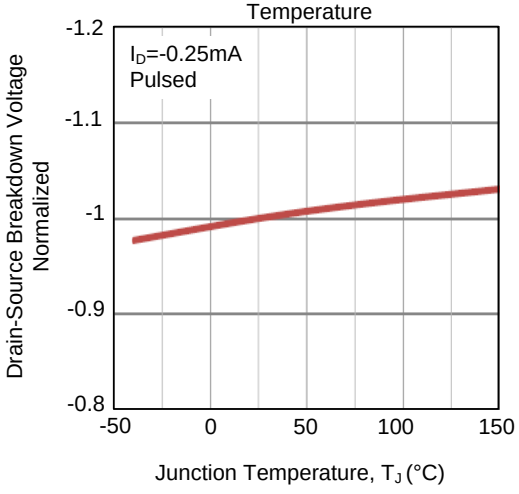
Body-Diode Continuous Current vs. Source to Drain Voltage



Drain-Source On-Resistance vs. Junction Temperature



Breakdown Voltage vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)